# **50 μV Offset, 0.25 μV/°C, 35 μA, Zero-Drift Operational Amplifier**

The NCS325, NCS2325 and NCS4325 are CMOS operational amplifiers providing precision performance. The Zero–Drift architecture allows for continuous auto–calibration, which provides very low offset, near–zero drift over time and temperature, and near flat 1/f noise at only 35  $\mu$ A (max) quiescent current. These benefits make these devices ideal for precision DC applications. These op amps provide rail–to–rail input and output performance and are optimized for low voltage operation as low as 1.8 V and up to 5.5 V. The single channel NCS325 is available in the space–saving SOT23–5 package. The dual channel NCS2325 is available in Micro8, SOIC–8, and DFN–8. The quad channel NCS4325 is available in SOIC–14.

#### Features

- Low Offset Voltage: 14 μV typ, 50 μV max at 25°C for NCS325
- Zero Drift: 0.25 µV/°C max
- Low Noise: 1 µVpp, 0.1 Hz to 10 Hz
- Quiescent Current: 21 μA typ, 35 μA max at 25°C
- Supply Voltage: 1.8 V to 5.5 V
- Rail-to-Rail Input and Output
- Internal EMI Filtering
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

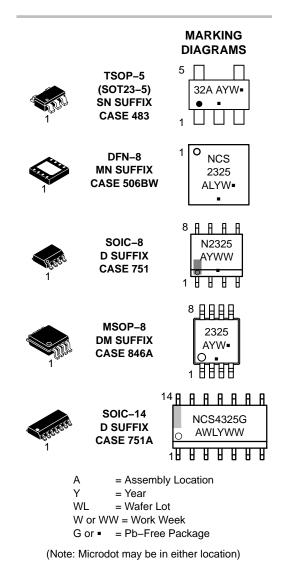
### **Typical Applications**

- Battery Powered Instruments
- Temperature Measurements
- Transducer Applications
- Electronic Scales
- Medical Instrumentation
- Current Sensing



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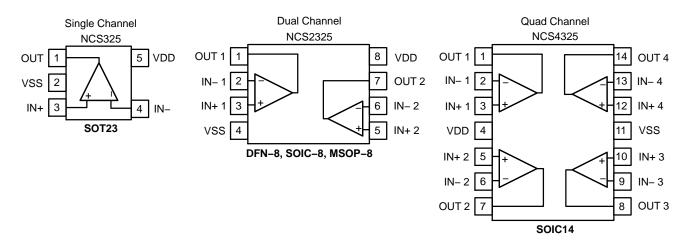


#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

This document contains information on some products that are still under development. ON Semiconductor reserves the right to change or discontinue these products without notice.

### **PIN CONNECTIONS**



#### **ORDERING INFORMATION**

Configuration	Device	Package	Shipping <sup>†</sup>
Single	NCS325SN2T1G	SOT23-5 / TSOP-5	3000 / Tape & Reel
Dual	NCS2325MNTXG* (In Development)	DFN8	3000 / Tape & Reel
	NCS2325DR2G	SOIC-8	3000 / Tape & Reel
	NCS2325DMR2G	Micro8 / MSOP-8	4000 / Tape & Reel
Quad	NCS4325DR2G	SOIC-14	2500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. \*Contact local sales office for more information

ABSOLUTE MAXIMUM RATINGS Over operating free-air temperature, unless otherwise stated.

Parameter	Rating	Unit	
Supply Voltage	6	V	
INPUT AND OUTPUT PINS		-	
Input Voltage (Note 1)	$(V_{SS}) - 0.3$ to $(V_{DD}) + 0.3$	V	
Input Current (Note 1)	±10	mA	
Output Short Circuit Current (Note 2)	Continuous		
TEMPERATURE			
Operating Temperature	-40 to +150	°C	
Storage Temperature	-65 to +150		
Junction Temperature	+150		
ESD RATINGS (Note 3)			
Human Body Model (HBM)	4000	V	
Machine Model (MM)	200	V	
OTHER RATINGS		-	

Latch-up Current (Note 4)	100	mA
MSL	Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.3 V beyond the supply rails should be current limited to 10 mA or less

2. Short-circuit to ground.

 This device series incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per AEC–Q100–002 (JEDEC standard: JESD22–A114) ESD Machine Model tested per AEC–Q100–003 (JEDEC standard: JESD22–A115)

4. Latch-up Current tested per JEDEC standard: JESD78.

### THERMAL INFORMATION

Thermal Metric	Symbol	Package	Value	Unit
Junction to Ambient (Note 5)	$\theta_{JA}$	SOT23-5 / TSOP-5	235	°C/W
		Micro8 / MSOP-8	298	
		SOIC-8	250	
		DFN-8	130	
		SOIC-14	216	

5. As mounted on an 80x80x1.5 mm FR4 PCB with 650 mm<sup>2</sup> and 2 oz (0.034 mm) thick copper heat spreader. Following JEDEC JESD/EIA 51.1, 51.2, 51.3 test guidelines

### **OPERATING CONDITIONS**

Parameter	Symbol	Range	Unit
Supply Voltage (V <sub>DD</sub> – V <sub>SS</sub> )	V <sub>S</sub>	1.8 to 5.5	V
Specified Operating Range	T <sub>A</sub>	-40 to 125	°C
Input Common Mode Voltage Range	V <sub>ICMR</sub>	V <sub>SS</sub> -0.1 to V <sub>DD</sub> +0.1	V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

**ELECTRICAL CHARACTERISTICS:**  $V_S = 1.8 V$  to 5.5 V At  $T_A = +25^{\circ}$ C,  $R_L = 10 k\Omega$  connected to midsupply,  $V_{CM} = V_{OUT} =$  midsupply, unless otherwise noted. **Boldface** limits apply over the specified temperature range,  $T_A = -40^{\circ}$ C to 125°C, guaranteed by characterization and/or design.

Parameter	Symbol		Conditions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS							
Offset Voltage	V <sub>OS</sub>	NCS325	V <sub>S</sub> = +5V		14	50	μV
		NCS2325, NCS4325	V <sub>S</sub> = +5V		14	75	
Offset Voltage Drift vs Temp	$\Delta V_{OS} / \Delta T$	-	T <sub>A</sub> = −40°C to 125°C		0.02	0.25	μV/°C
Input Bias Current	I <sub>IB</sub>				±50		pА
Input Offset Current	I <sub>OS</sub>				±100		pА
Common Mode Rejection Ratio	CMRR	NCS325	$V_{SS}$ +0.3 < $V_{CM}$ < $V_{DD}$ – 0.3, $V_{S}$ = 1.8 V	85	108		dB
			$V_{SS}$ +0.3 < $V_{CM}$ < $V_{DD}$ – 0.3, $V_{S}$ = 5.5 V	90	110		
		NCS2325, NCS4325	$V_{SS}$ +0.3 < $V_{CM}$ < $V_{DD}$ – 0.3, $V_{S}$ = 5 V	90	110		
		$V_{SS}$ -0.1 < $V_{CM}$ < $V_{DD}$ + 0.1, $V_{S}$ = 1.8 V			80		
		V <sub>SS</sub> -0.1 <	< V <sub>CM</sub> < V <sub>DD</sub> + 0.1, V <sub>S</sub> = 5.5 V		92		
Input Resistance	R <sub>IN</sub>				15		GΩ
Input Capacitance	C <sub>IN</sub>	NCS325	Differential		1.8		pF
			Common Mode		3.5		pF
		NCS2325,	Differential		4.1		pF
		NCS4325	Common Mode		8.0		pF
OUTPUT CHARACTERISTICS							
Output Voltage High	V <sub>OH</sub>	Ou	utput swing within V <sub>DD</sub>		12	100	mV
Output Voltage Low	V <sub>OL</sub>	0	utput swing within V <sub>SS</sub>		8	100	mV
Short Circuit Current	I <sub>SC</sub>				±5		mA
Open Loop Output Impedance	Z <sub>out-OL</sub>	f = 350	kHz, $I_{O}$ = 0 mA, $V_{S}$ = 1.8 V		1.4		kΩ
		f = 350	kHz, $I_{O}$ = 0 mA, $V_{S}$ = 5.5 V		2.7		
Capacitive Load Drive	CL				See Figure	)	
NOISE PERFORMANCE							
Voltage Noise Density	<b>EN</b>		fuu = 1 kHz		100		nV / √H

Voltage Noise Density	e <sub>N</sub>	f <sub>IN</sub> = 1 kHz	100	nV / √Hz
Voltage Noise	ep-p	f <sub>IN</sub> = 0.01 Hz to 1 Hz	0.3	$\mu V_{PP}$
		f <sub>IN</sub> = 0.1 Hz to 10 Hz	1	$\mu V_{PP}$
Current Noise Density	i <sub>N</sub>	f <sub>IN</sub> = 10 Hz	0.3	pA / √ <del>Hz</del>

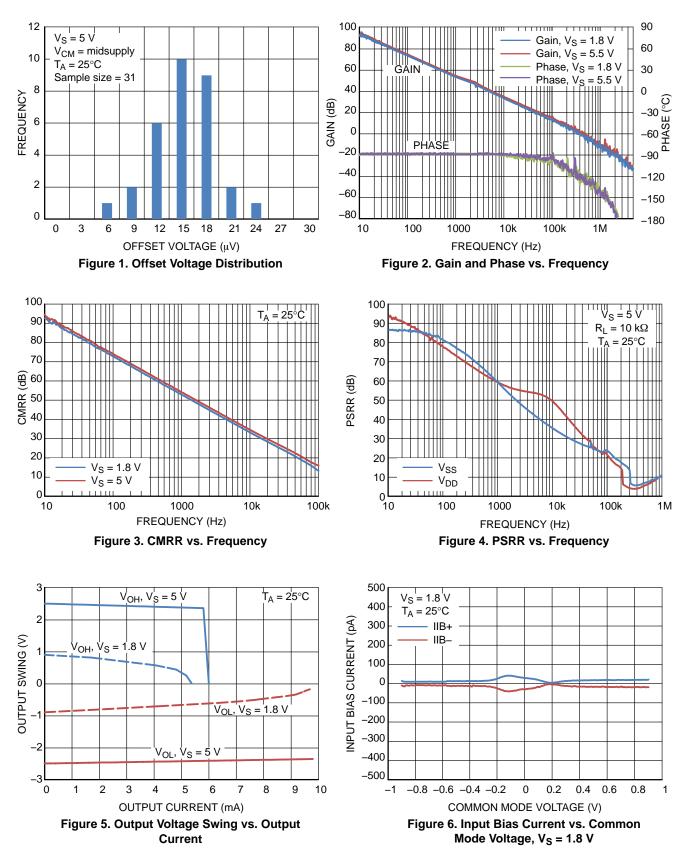
#### DYNAMIC PERFORMANCE

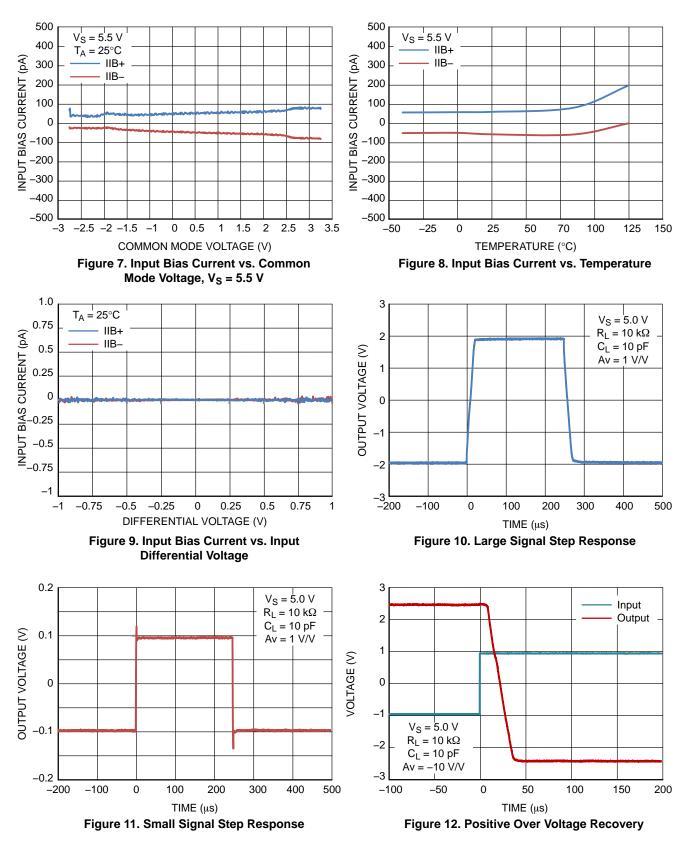
Open Loop Voltage Gain	A <sub>VOL</sub>	$R_L$ = 10 kΩ, $V_S$ = 5.5 V		114	dB
Gain Bandwidth Product	GBWP	NCS325	$C_L$ = 100 pF, $R_L$ = 10 k $\Omega$	350	kHz
		NCS2325, NCS4325	$C_L$ = 100 pF, $R_L$ = 10 k $\Omega$	270	
Phase Margin	$\phi_{M}$	C <sub>L</sub> = 100 pF		60	0
Gain Margin	A <sub>M</sub>		C <sub>L</sub> = 100 pF	20	dB
Slew Rate	SR	G = +1, C <sub>L</sub> = 100 pF, Vs = 1.8 V		0.10	V/μs
		G = +	1, C <sub>L</sub> = 100 pF, Vs = 5.5 V	0.16	

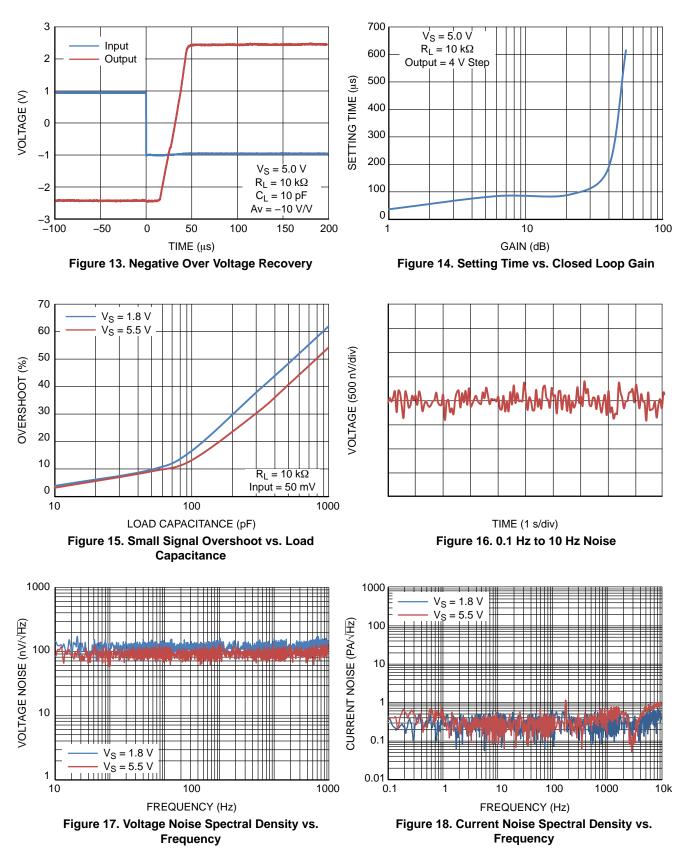
#### POWER SUPPLY

Power Supply Rejection Ratio	PSRR		100	107		dB
		$T_A = -40^{\circ}C$ to $125^{\circ}C$	95			
Turn–on Time	t <sub>ON</sub>	$V_{S} = 5 V$		100		μs
Quiescent Current	Ι <sub>Q</sub>	No load		21	35	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.







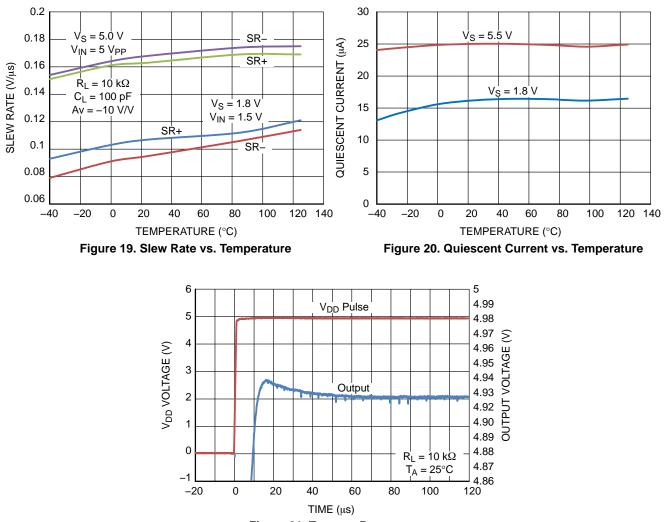


Figure 21. Turn-on Response

### **APPLICATIONS INFORMATION**

### INPUT VOLTAGE

The NCS325, NCS2325 and NCS4325 have rail-to-rail common mode input voltage range. Diodes between the inputs and the supply rails keep the input voltage from exceeding the rails.

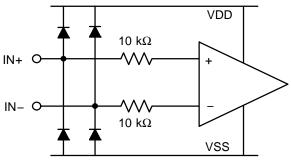


Figure 22. Equivalent Input Circuit

### EMI SUSCEPTIBILITY AND INPUT FILTERING

Op amps have varying amounts of EMI susceptibility. Semiconductor junctions can pick up and rectify EMI signals, creating an EMI–induced voltage offset at the output, adding another component to the total error. Input pins are the most sensitive to EMI. The NCS325, NCS2325 and NCS4325 integrate a low–pass filter to decrease its sensitivity to EMI.

### **APPLICATION CIRCUITS**

### Low-Side Current Sensing

The goal of low-side current sensing is to detect over-current conditions or as a method of feedback control. A sense resistor is placed in series with the load to ground. Typically, the value of the sense resistor is less than 100 m $\Omega$ to reduce power loss across the resistor. The op amp amplifies the voltage drop across the sense resistor with a gain set by external resistors R1, R2, R3, and R4 (where R1 = R2, R3 = R4). Precision resistors are required for high accuracy, and the gain is set to utilize the full scale of the ADC for the highest resolution.

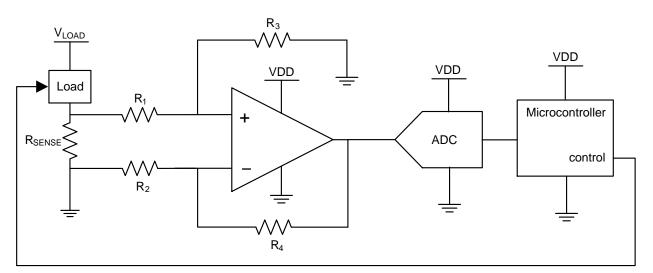


Figure 23. Low-Side Current Sensing

### **Differential Amplifier for Bridged Circuits**

Sensors to measure strain, pressure, and temperature are often configured in a Wheatstone bridge circuit as shown in Figure 24. In the measurement, the voltage change that is produced is relatively small and needs to be amplified before going into an ADC. Precision amplifiers are recommended in these types of applications due to their high gain, low noise, and low offset voltage.

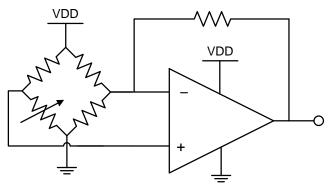
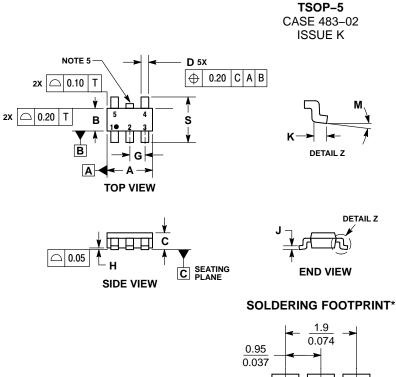


Figure 24. Bridge Circuit Amplification

### **GENERAL LAYOUT GUIDELINES**

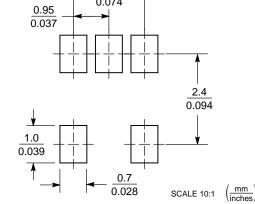
To ensure optimum device performance, it is important to follow good PCB design practices. Place  $0.1 \,\mu\text{F}$  decoupling capacitors as close as possible to the supply pins. Keep traces short, utilize a ground plane, choose surface-mount components, and place components as close as possible to

the device pins. These techniques will reduce susceptibility to electromagnetic interference (EMI). Thermoelectric effects can create an additional temperature dependent offset voltage at the input pins. To reduce these effects, use metals with low thermoelectric–coefficients and prevent temperature gradients from heat sources or cooling fans.

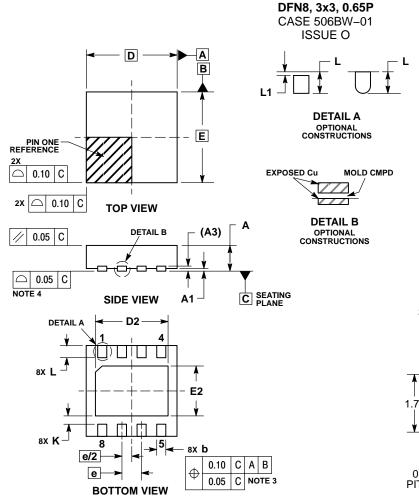


- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 4. DIMENSIONIS A AND R DO NOT INCLUDE MOLD
- MINIMUM THICKNESS OF BASE WATEKIAL. 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A. 5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD IN TA CATEND MODE TUAN 0.2
- TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

-	-				
	MILLIMETERS				
DIM	MIN MAX				
Α	3.00	BSC			
В	1.50 BSC				
С	0.90	1.10			
D	0.25	0.50			
G	0.95	BSC			
н	0.01	0.10			
J	0.10	0.26			
к	0.20	0.60			
м	0 °	10 °			
S	2.50	3.00			



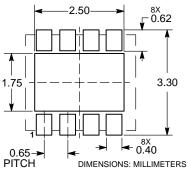
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



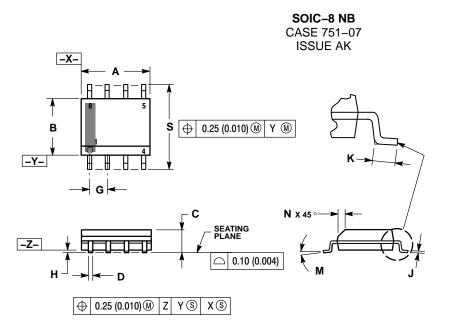
- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm EPOM THE TERMINAL TIP
- 0.30mm FROM THE TERMINAL TIP.
  4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIM	ETERS
DIM	MIN	MAX
Α	0.80	1.00
A1	0.00	0.05
A3	0.20	REF
b	0.25	0.35
D	3.00	BSC
D2	2.30	2.50
Е	3.00	BSC
E2	1.55	1.75
е	0.65	BSC
κ	0.20	
L	0.35	0.45
L1	0.00	0.15

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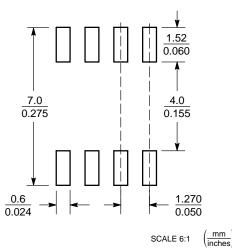


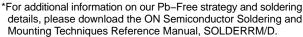
- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION. 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) DEEP SIDE

- PER SIDE. 5. DIMENSION D DOES NOT INCLUDE DAMBAR
- DIMENSION DOES NOT INCLODE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION. 751-01 THRU 751-06 ARE OBSOLETE. NEW CTANDAD IS 751-06
- 6. STANDARD IS 751-07.

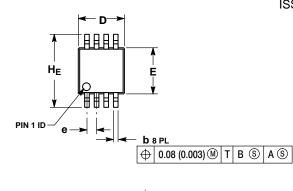
	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
κ	0.40	1.27	0.016	0.050	
Μ	0 °	8 °	0 °	8 °	
Ν	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

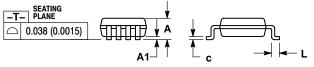
**SOLDERING FOOTPRINT\*** 





Micro8<sup>™</sup> CASE 846A-02 **ISSUE J** 

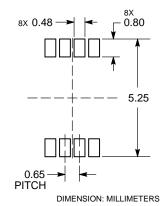




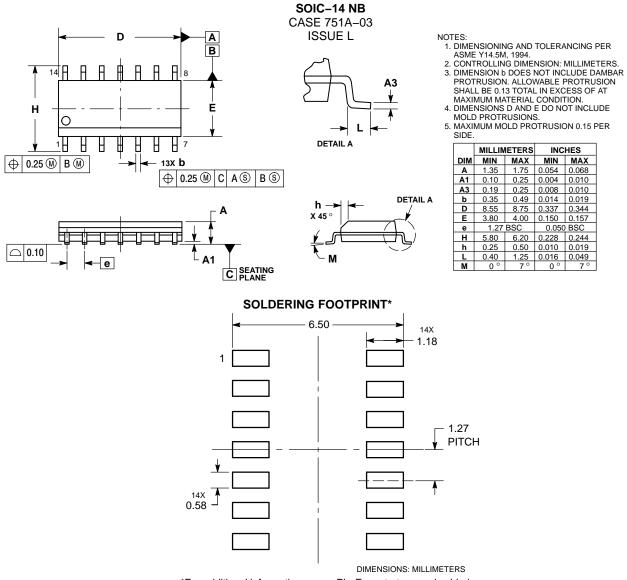
- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE DIMENSION ADDES NOT INCLUDE INCLUDE INCLUDE INCLUDE TASTI, FROTTUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS OF GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
   DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- 5. 846A-01 OBSOLETE, NEW STANDARD 846A-02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.05	0.08	0.15	0.002	0.003	0.006
b	0.25	0.33	0.40	0.010	0.013	0.016
С	0.13	0.18	0.23	0.005	0.007	0.009
D	2.90	3.00	3.10	0.114	0.118	0.122
Е	2.90	3.00	3.10	0.114	0.118	0.122
е	0.65 BSC			0.026 BSC		
L	0.40	0.55	0.70	0.016	0.021	0.028
HE	4.75	4.90	5.05	0.187	0.193	0.199

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